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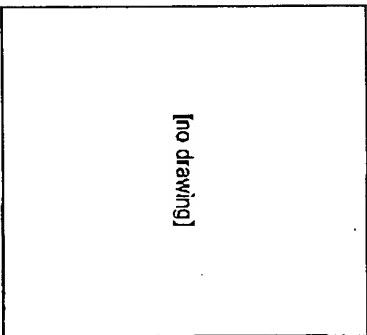
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JP2004133384 A
RESIST REMOVING AGENT
COMPOSITION AND METHOD FOR
MANUFACTURING
SEMICONDUCTOR DEVICE
SONY CORP EKC TECHNOLOGY KK

Abstract:

PROBLEM TO BE SOLVED: To provide a resist removing agent composition having such components that photoresist residues or polymers after dry etching are easily removed and an insulating film with a low dielectric constant is not corroded or oxidized.SOLUTION: One



example of the resist removing agent composition comprises: 5.0 wt. % of sulfamic acid, 34.7 wt. % of H₂O, 0.3 wt. % of ammonium hydrogendifluoride, 30 wt. % of N, N dimethyl acetamide; and 30 wt. % of ethyleneglycol mono n-butylether. Another example of the resist removing agent composition comprises: 3.0 wt. % of 1-hydroxyethylene-1,1-diphosphonic acid, 0.12 wt. % of ammonium fluoride, 48.4 wt. % of H₂O, and 48.5 wt. % of diethyleneglycol mono n-butylether. The resist removing agent composition is primarily used as a chemical cleaning liquid to remove the resist residue and byproduct polymers after the ashing process of a resist mask.

Inventor(s):

MURAMATSU MASAFUMI
IWAMOTO ISATO
ASADA KAZUMI
SUZUKI TOMOKO
HIRAGA TOSHITAKA
AOYAMA TETSUO

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H01L021027 H01L021304 H01L021788

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